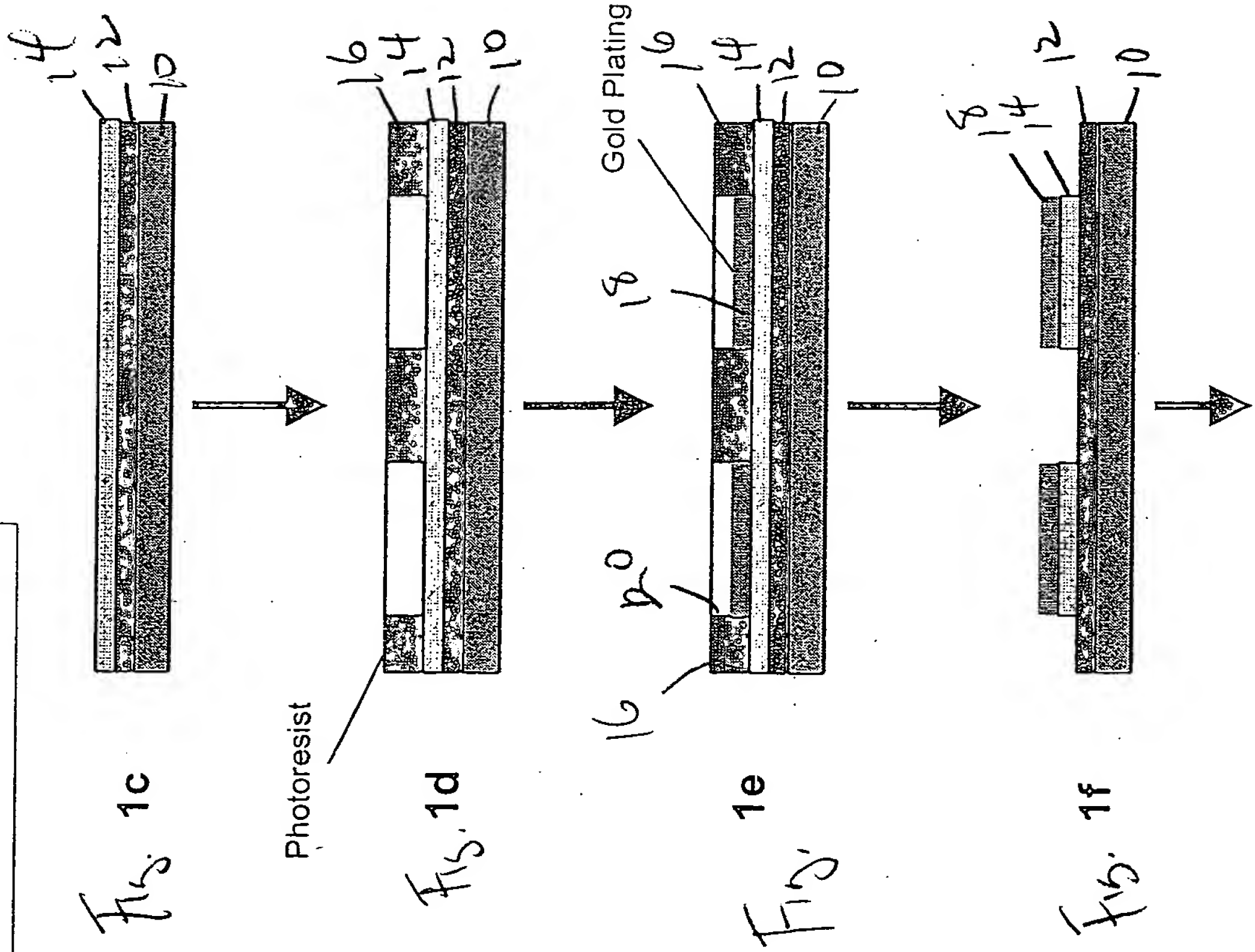


# Patented Reverse Neo Process

IRVINE SENSORS CORPORATION



- 1c) Apply field metal
- 1d) Apply photoresist
- 1e) Gold electroplate
- 1f) Strip photoresist & field metal etch

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# Reverse Neo Process

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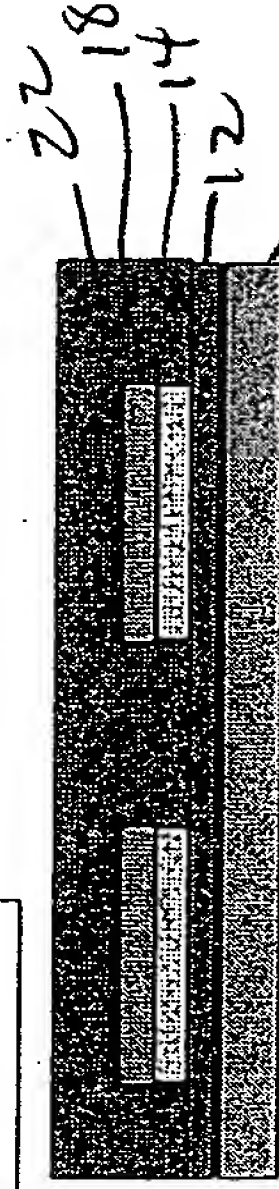


Fig 1g

1g) Apply polyimide

1h) Apply photoresist

1i) Image & develop photoresist & polyimide

1j) Strip photoresist & cure polyimide

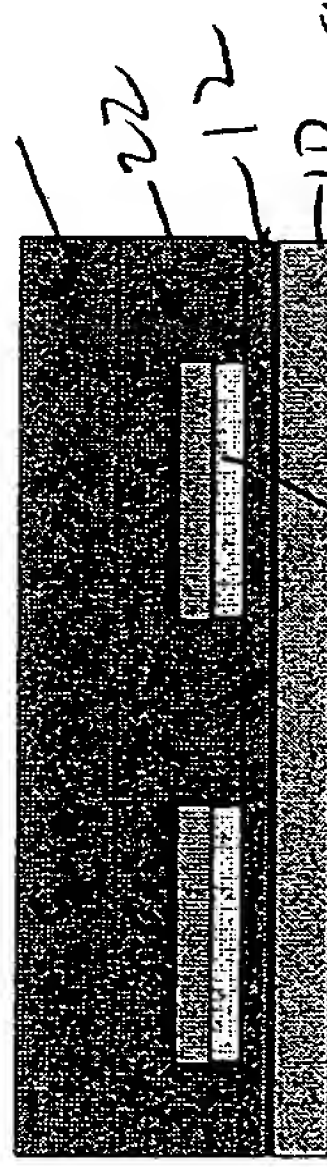


Fig 1h

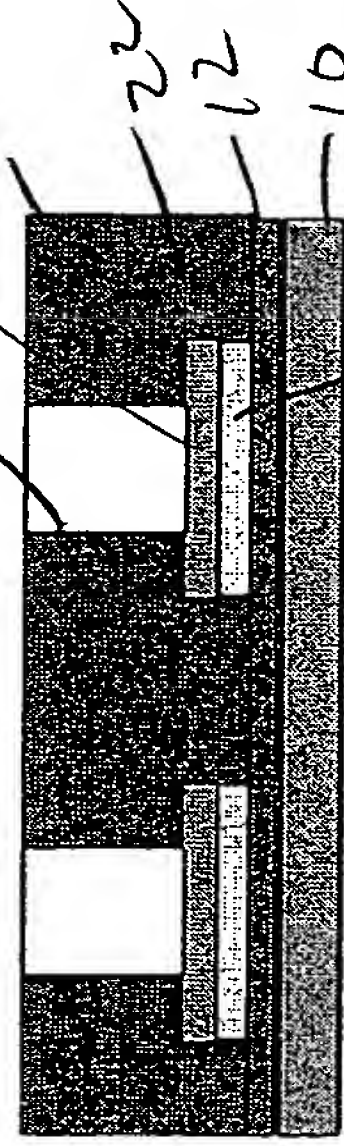


Fig 1i



Fig 1j

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# Reverse Neo Process

IRVINE SENSORS CORPORATION

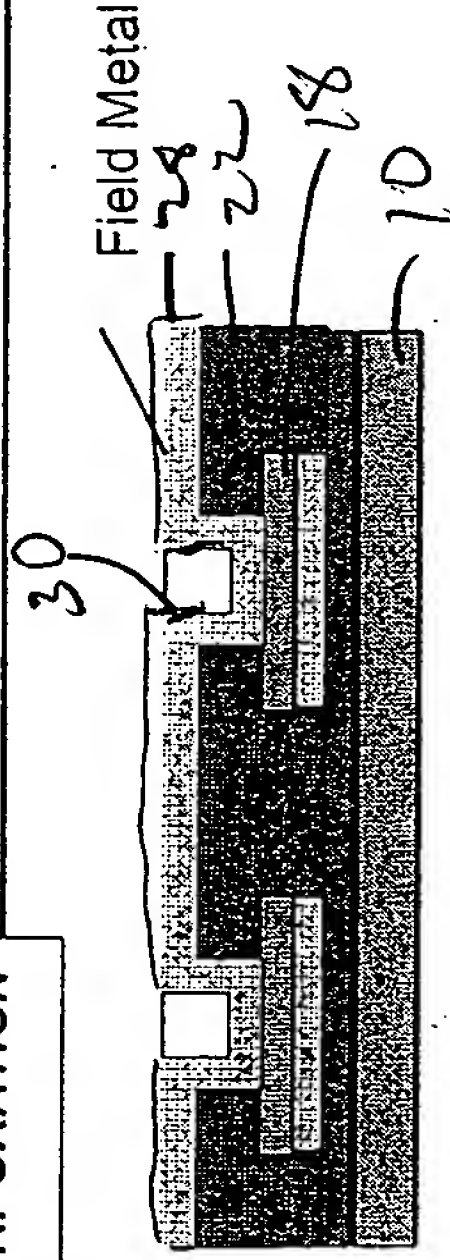


Fig. 1k

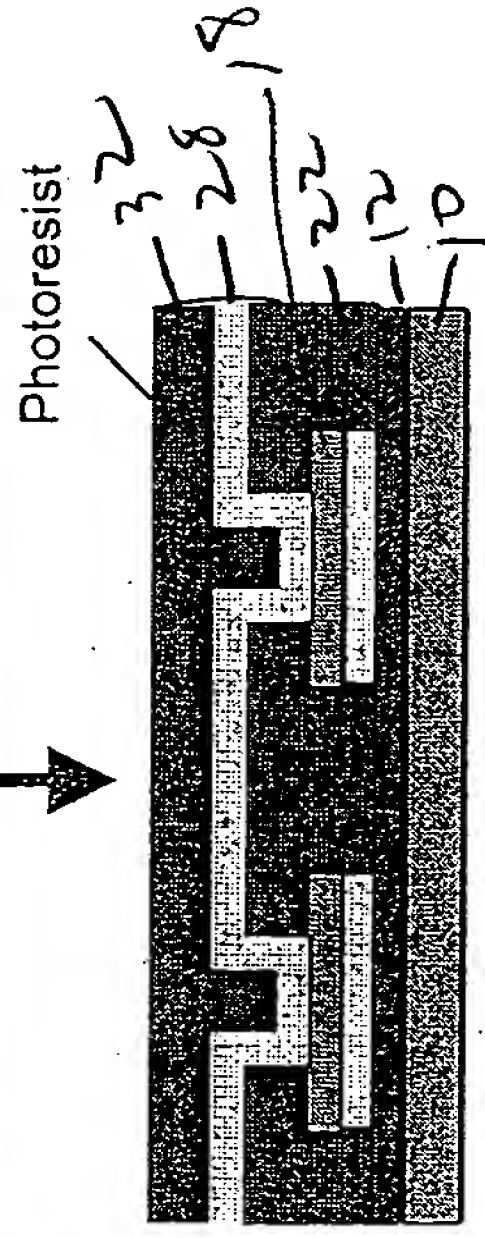


Fig. 1l

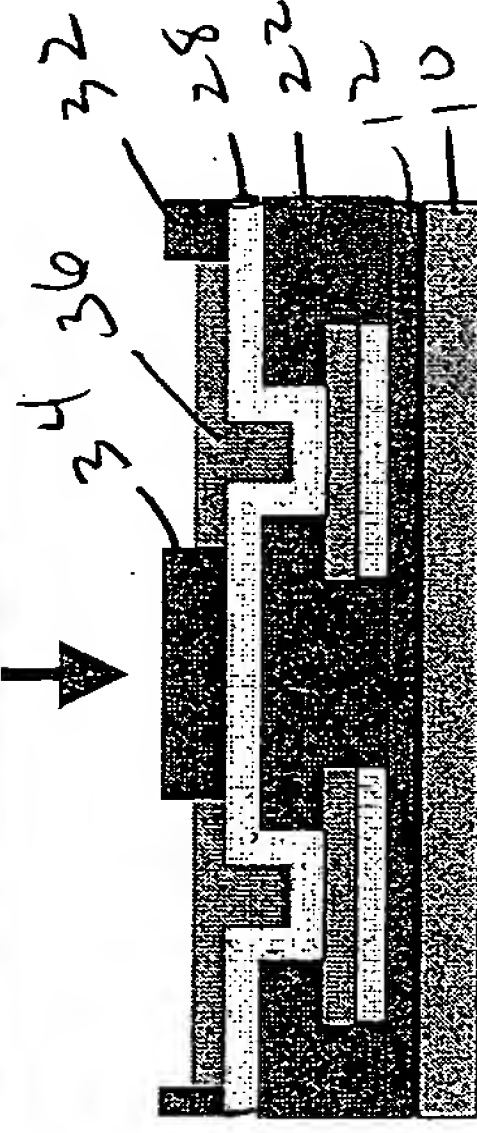


Fig. 1m

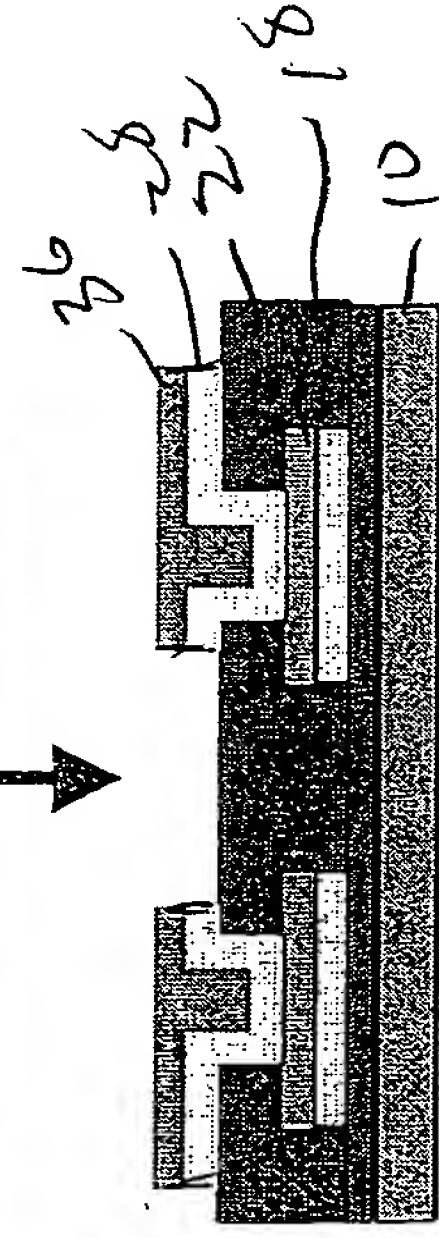


Fig. 1n

- 1k) Apply field metal
- 1l) Apply photoresist
- 1m) Image & develop photoresist. Gold electroplate
- 1n) Strip photoresist & field metal etch

NOTE: For additional layers, steps 1g through 1n are repeated.

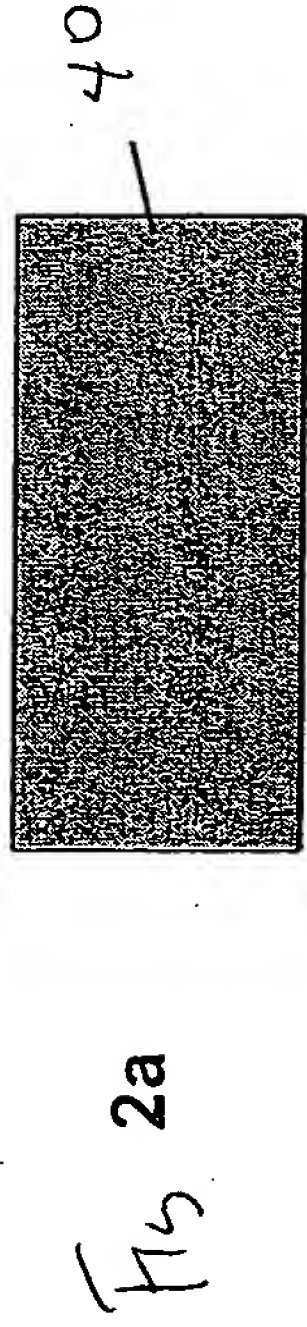
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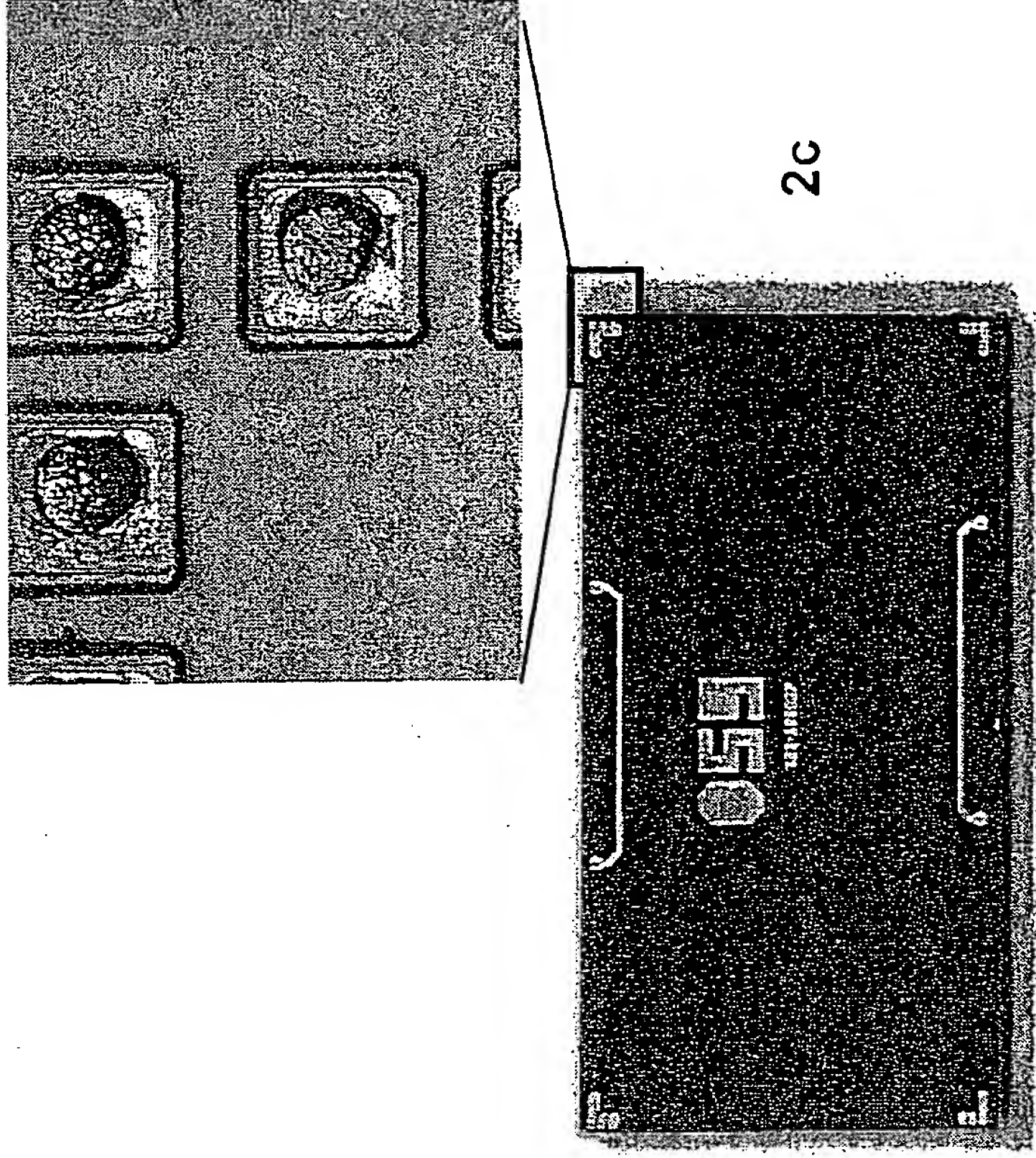
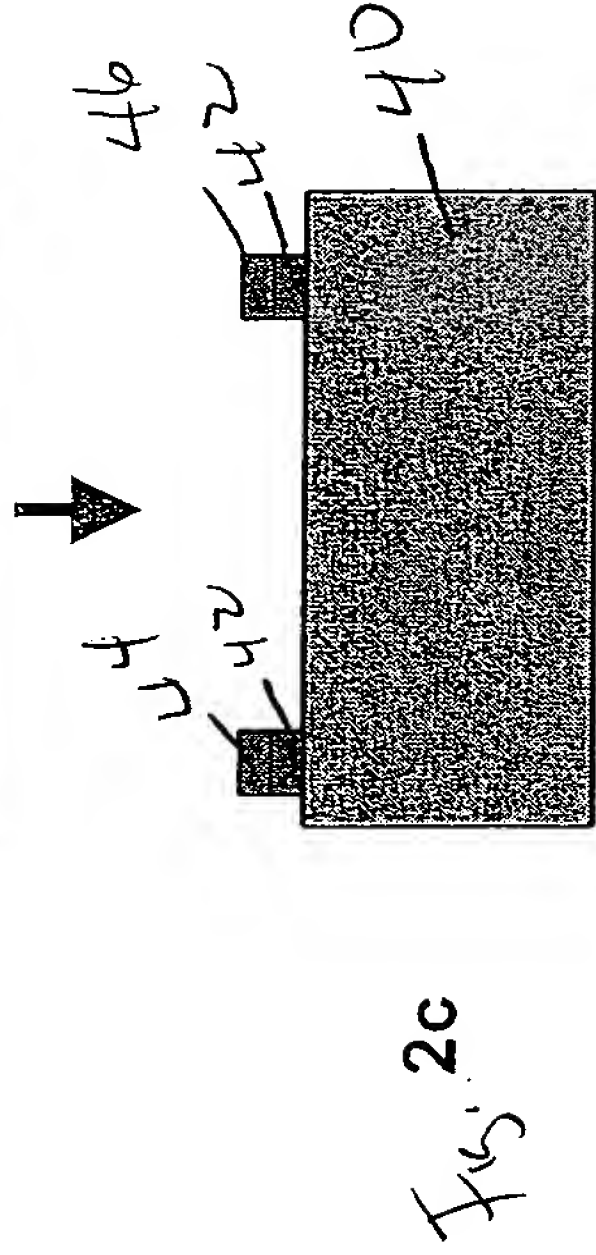
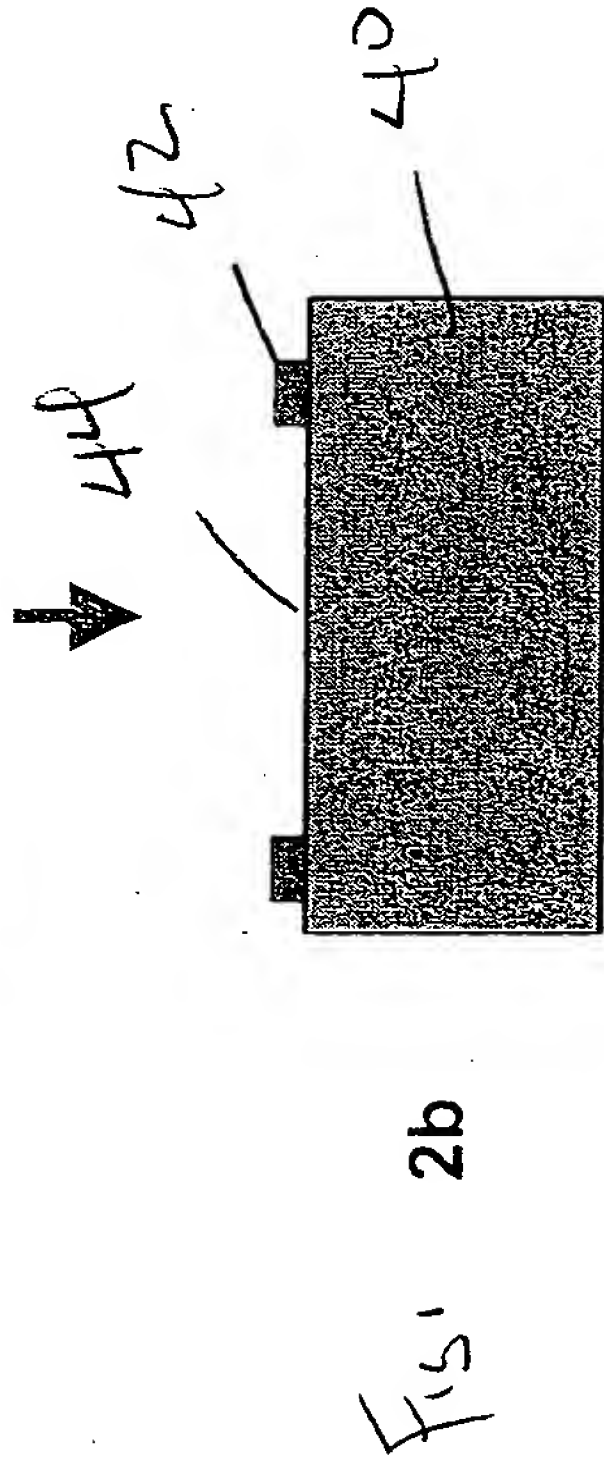
# FIG. 1 Reverse Neo Process

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### Solder Bumping Of Die



- 2a) Retrieve die
- 2b) Apply underbump metalurgy
- 2c) Apply solder bump



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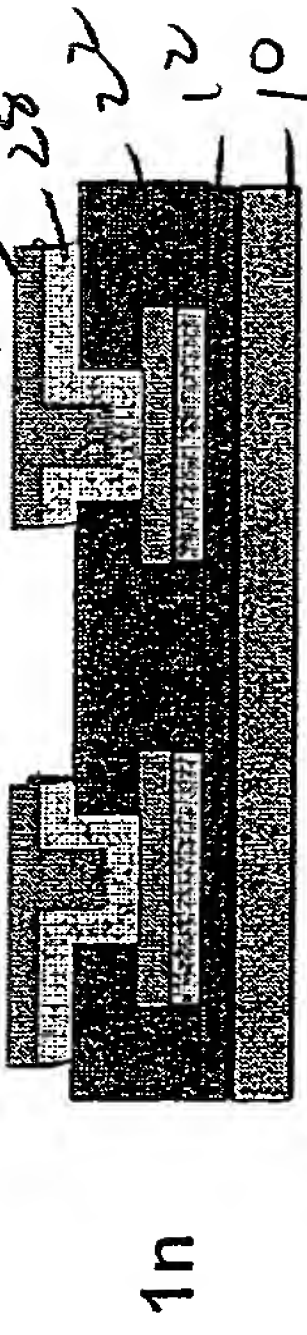
# Patented 5658660 Reverse Neo Process

IRVINE SENSORS CORPORATION

### Flip-Chip Bonding

Fig. 3a

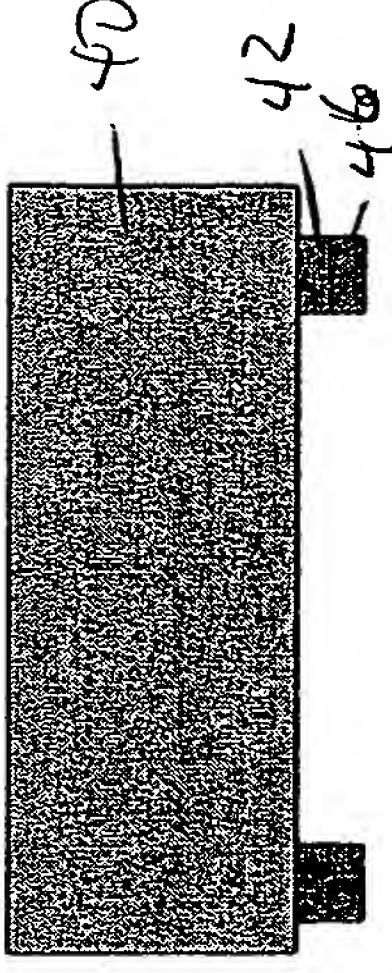
Retrieve substrate assembly and  
bumped die



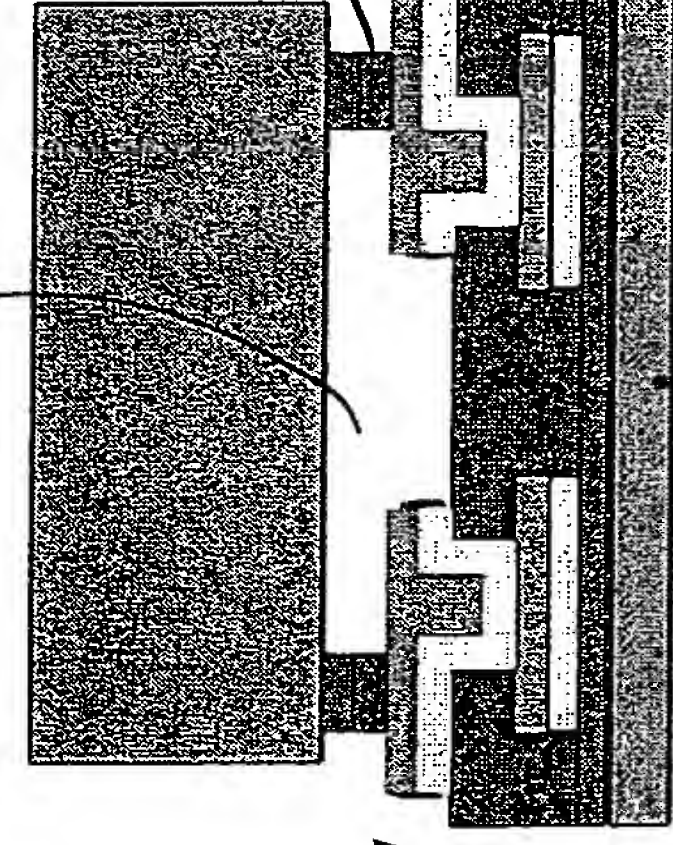
1n

2c

50



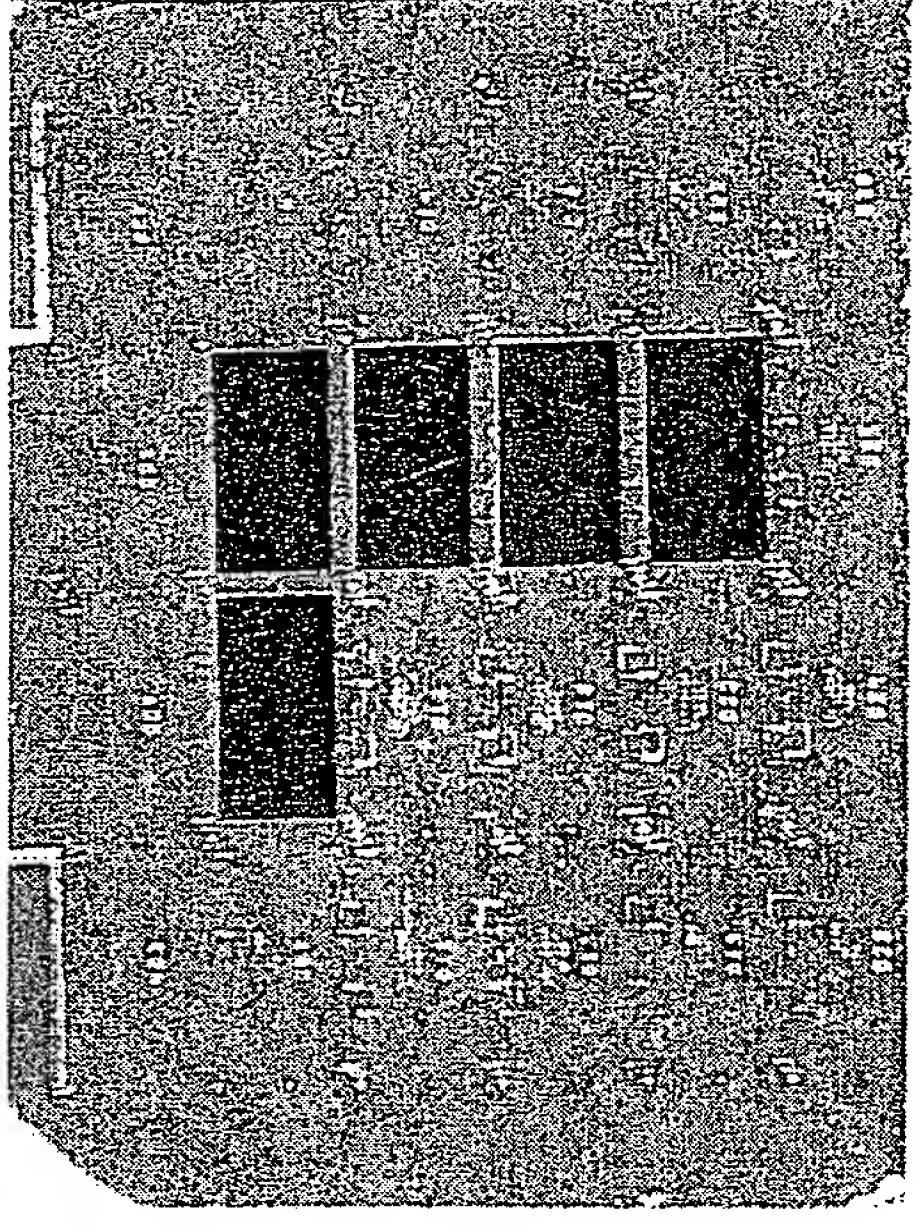
52



3a

48

3a) Flip chip bumped die to substrate



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FIG. 3a

# Reverse Neo Process

IRVINE SENSORS CORPORATION

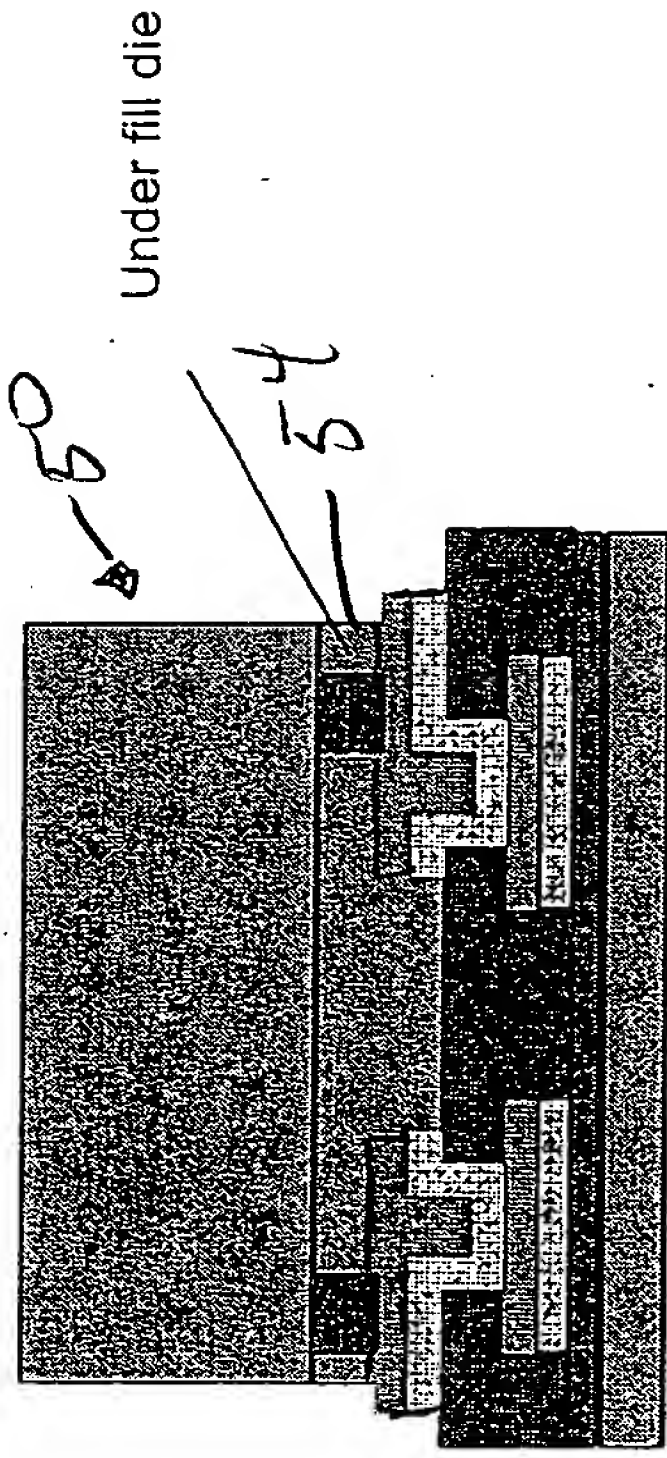


Fig 3b

- 3b) Underfill die
- 3c) Pot die

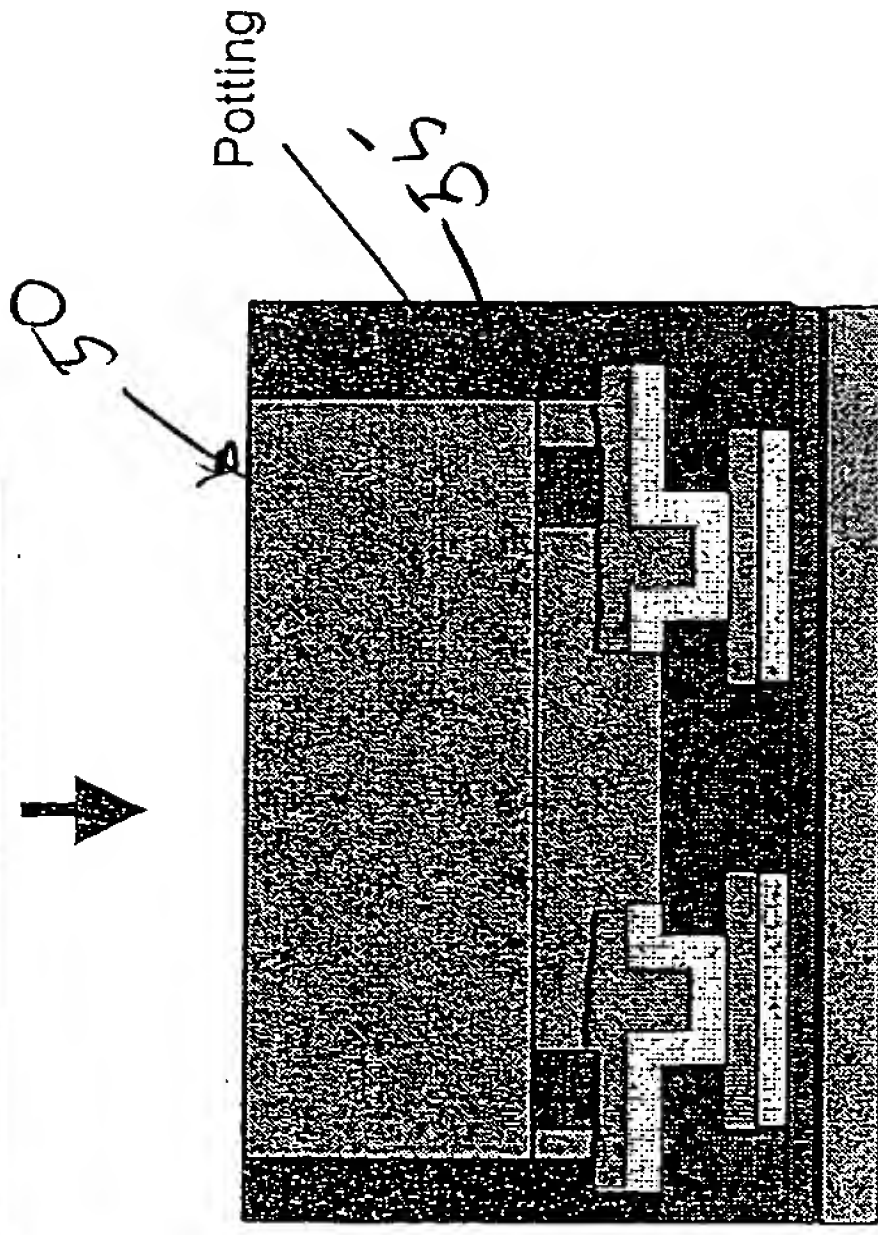


Fig 3c

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# Thin Silicon Reverse Neo Process

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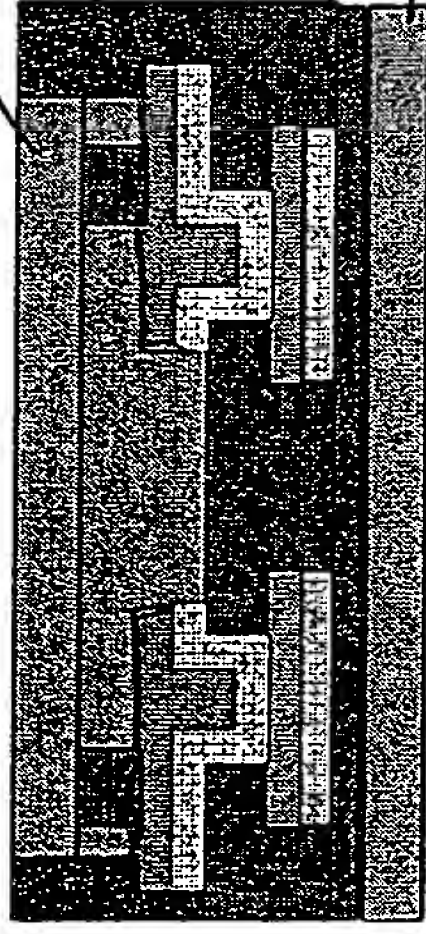


Fig. 3d

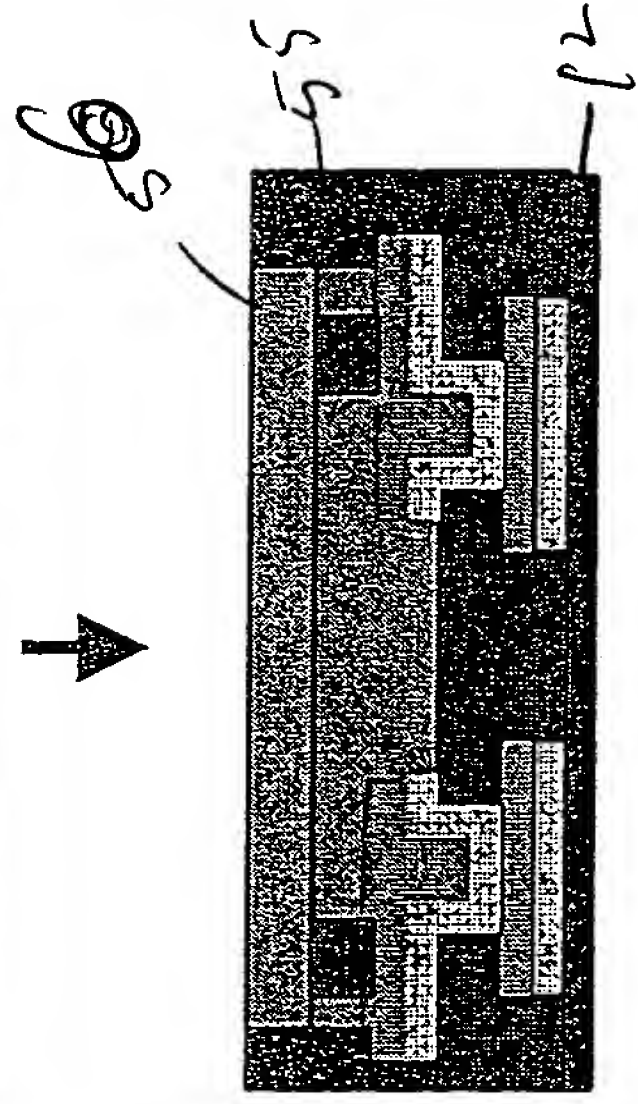
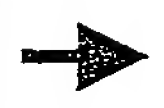


Fig. 3e

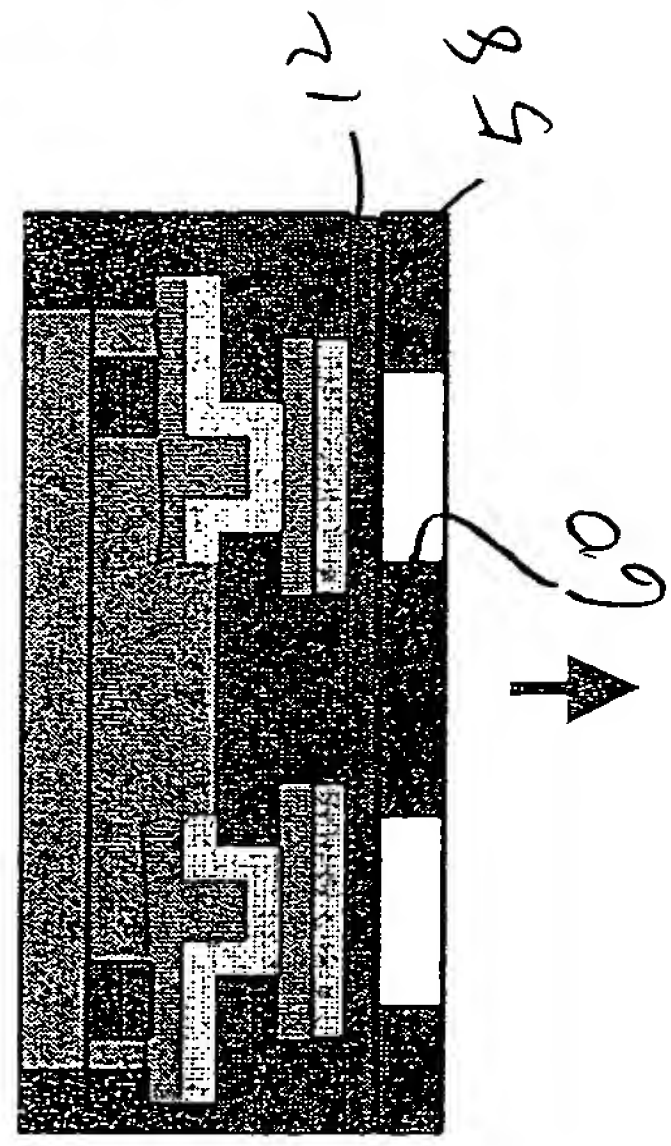
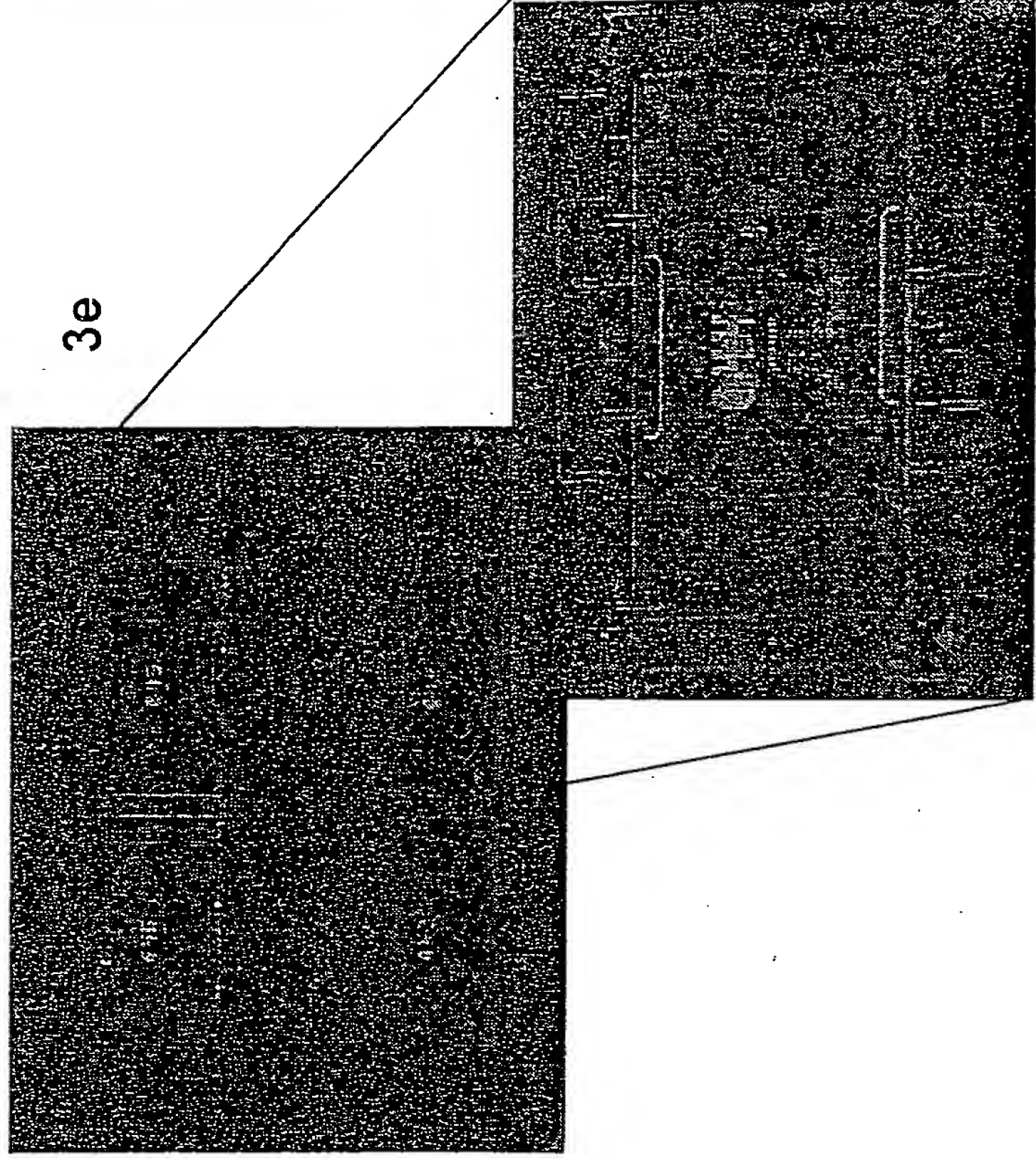


Fig. 3f



- 3d) Thin wafer
- 3e) Release wafer from aluminum substrate
- 3f) Mask wafer for test pad etch

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# Reverse Neo Process

IRVINE SENSORS CORPORATION

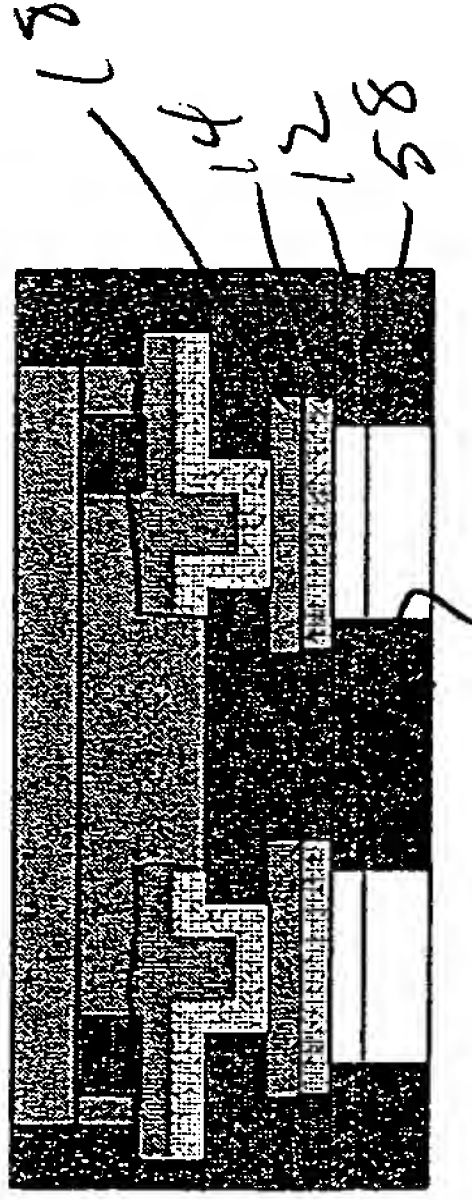


Fig 3g

- 3g) Etch polyimide to expose test pads
- 3h) Remove etch mask & test wafer
- 3i) Dice wafer

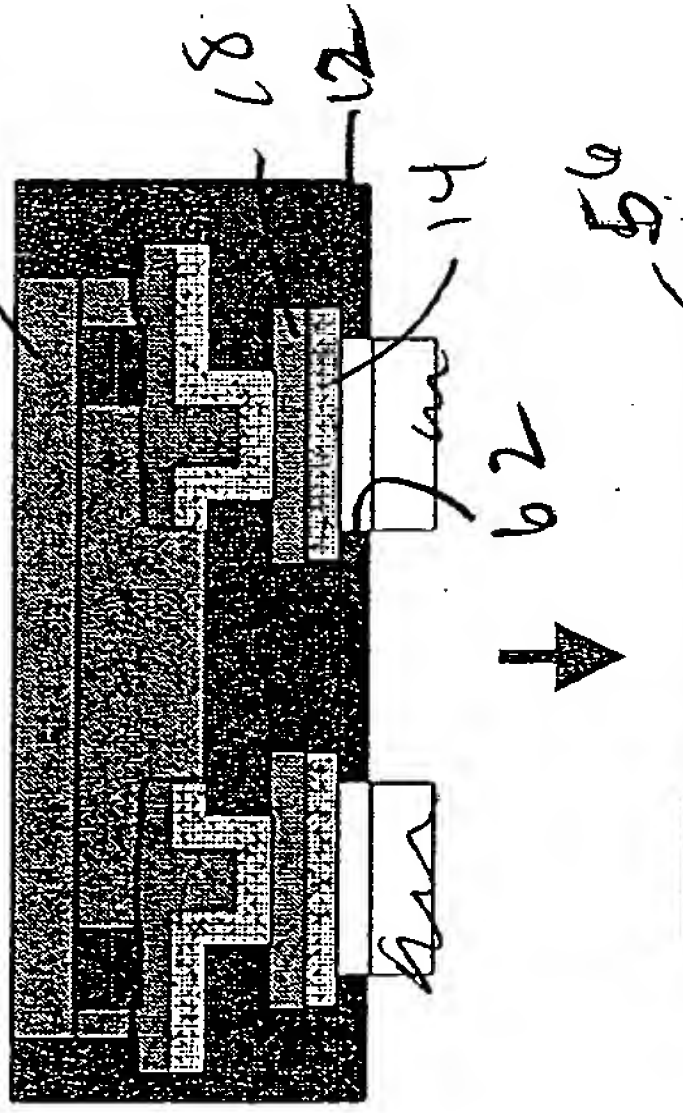


Fig 3h

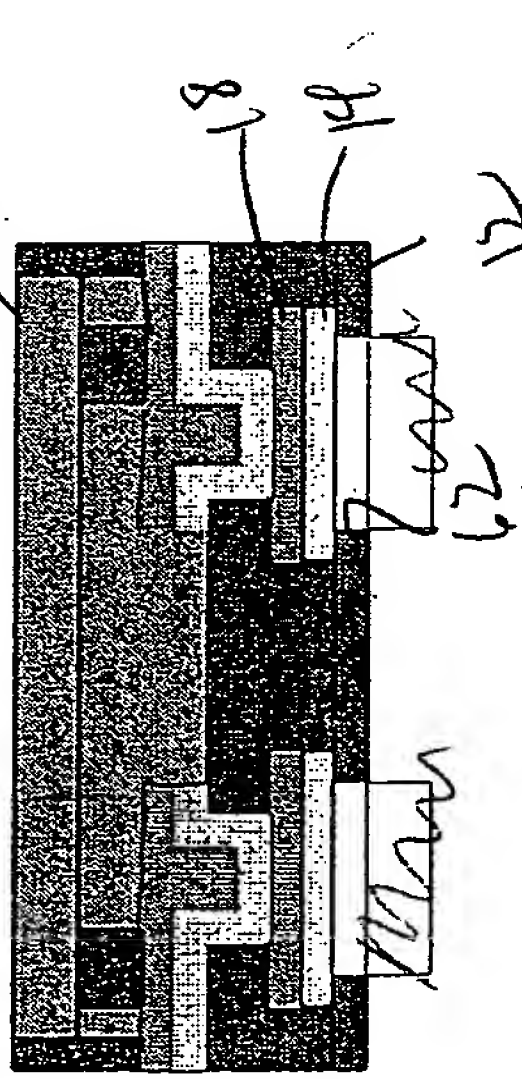


Fig 3i

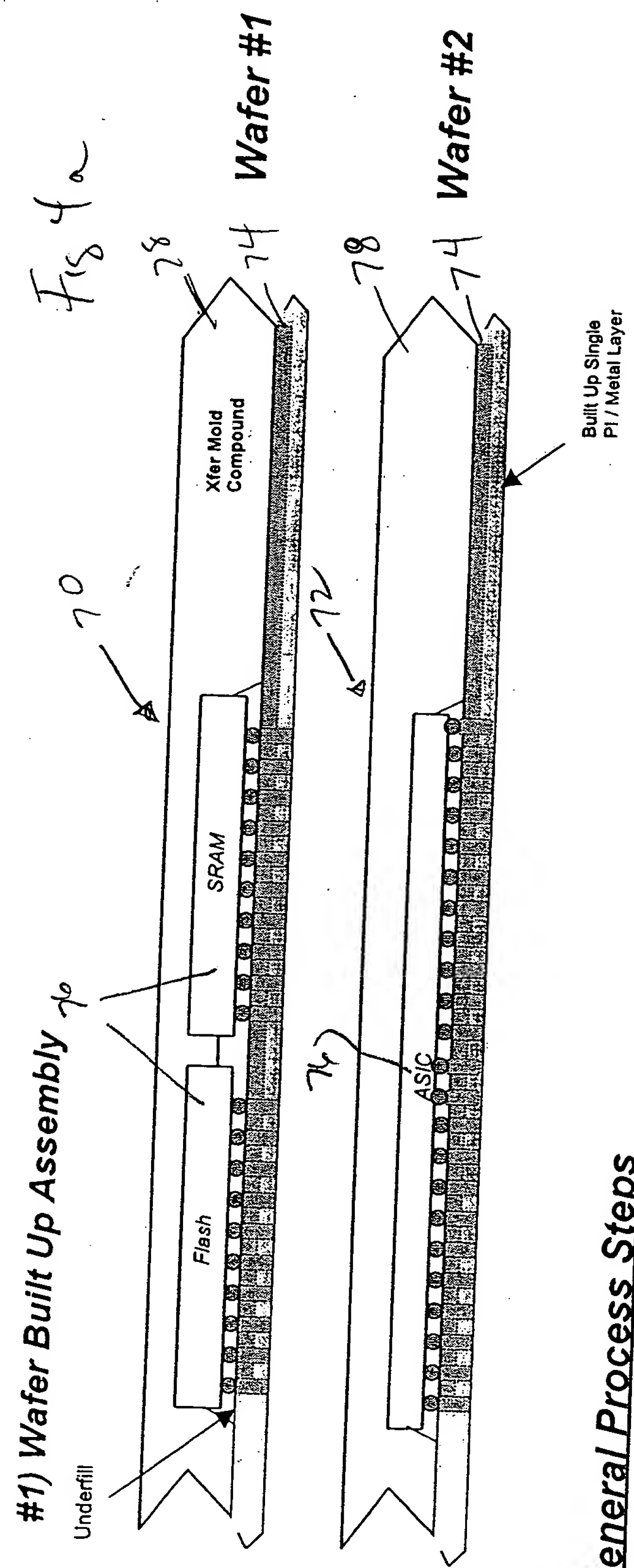
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#

FIGURE 3-33333333

# High Volume Reverse NEO Process



## General Process Steps

- 1) Screen Print Electrically Conductive Epoxy on Built-Up Laminate Substrates
- 2) Place Flip Chip Devices
- 3) Cure Epoxy
- 4) Underfill Devices
- 5) Xfer. Mold Devices

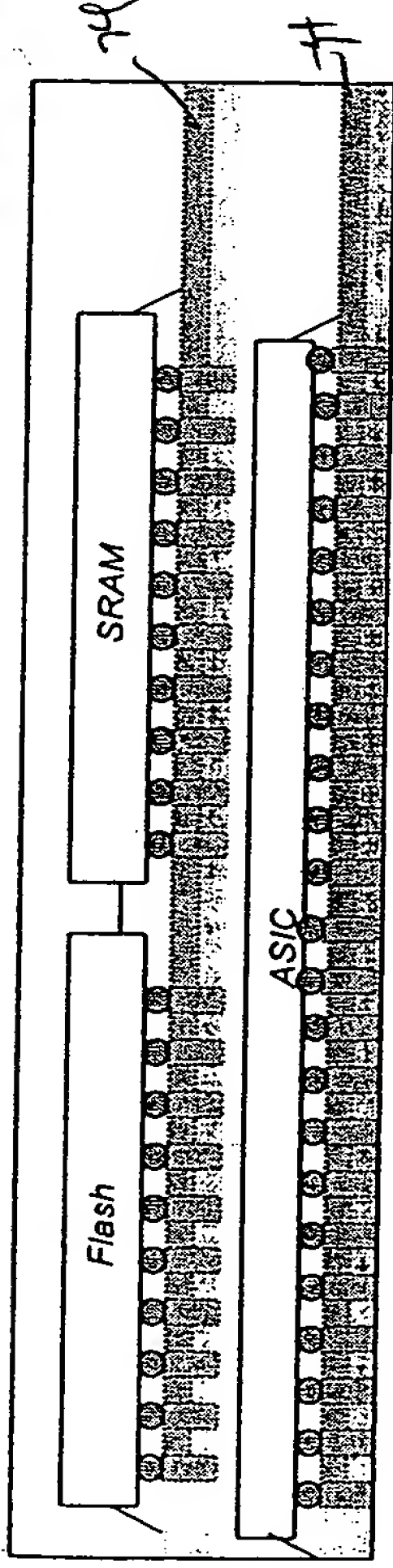
ISC - MPD

# High Volume Reverse NEO Process

2) Stacked Wafer Strip Assembly

Fig. 40  
40-1

## General Process Steps

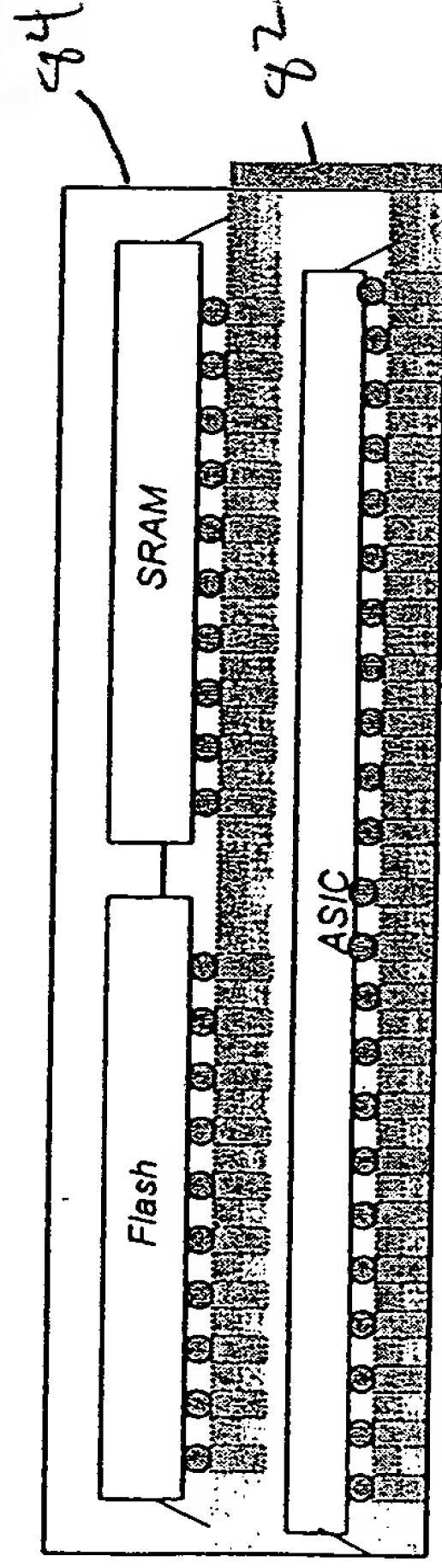


- 6) Release Carrier Film from Substrate (If Required)
- 7) Attach Memory and ASIC Wafers
- 8) Cut/Saw Wafers to Strips

3) Stacked Wafer Strip Assembly

Fig. 40  
40-2

## General Process Steps



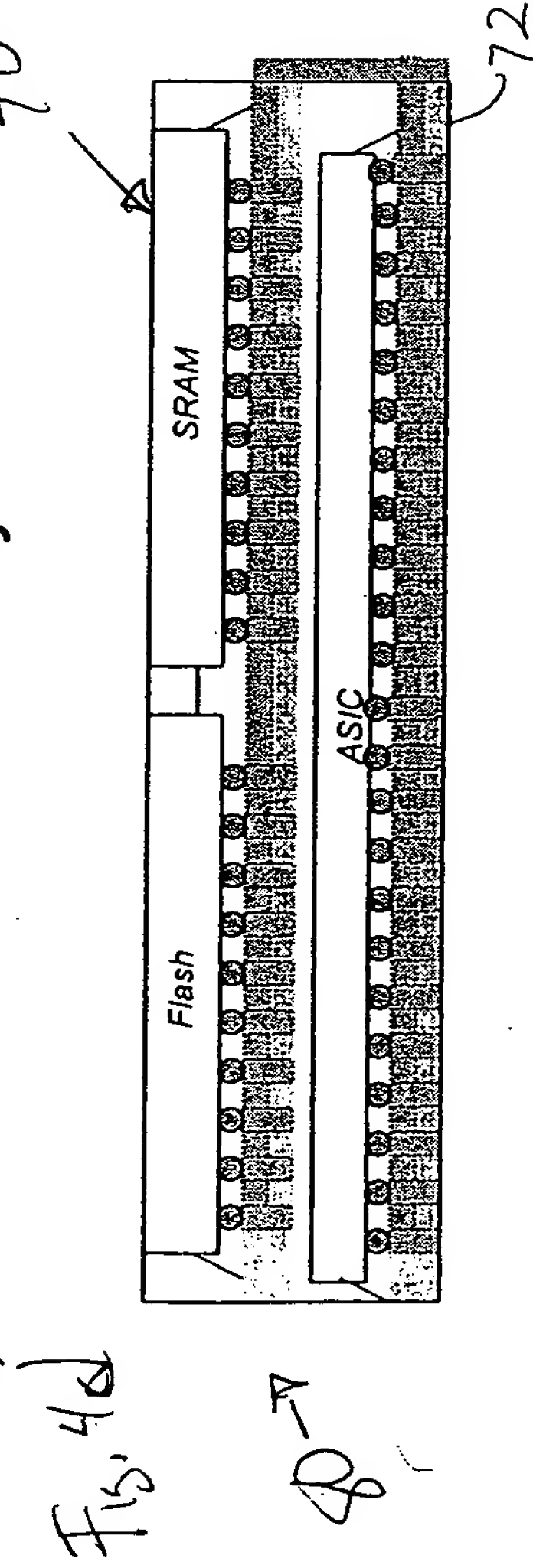
- 9) Interconnect or Bus Wafers by Metallizing Wafer Stacks



# High Volume Reverse NEO Process

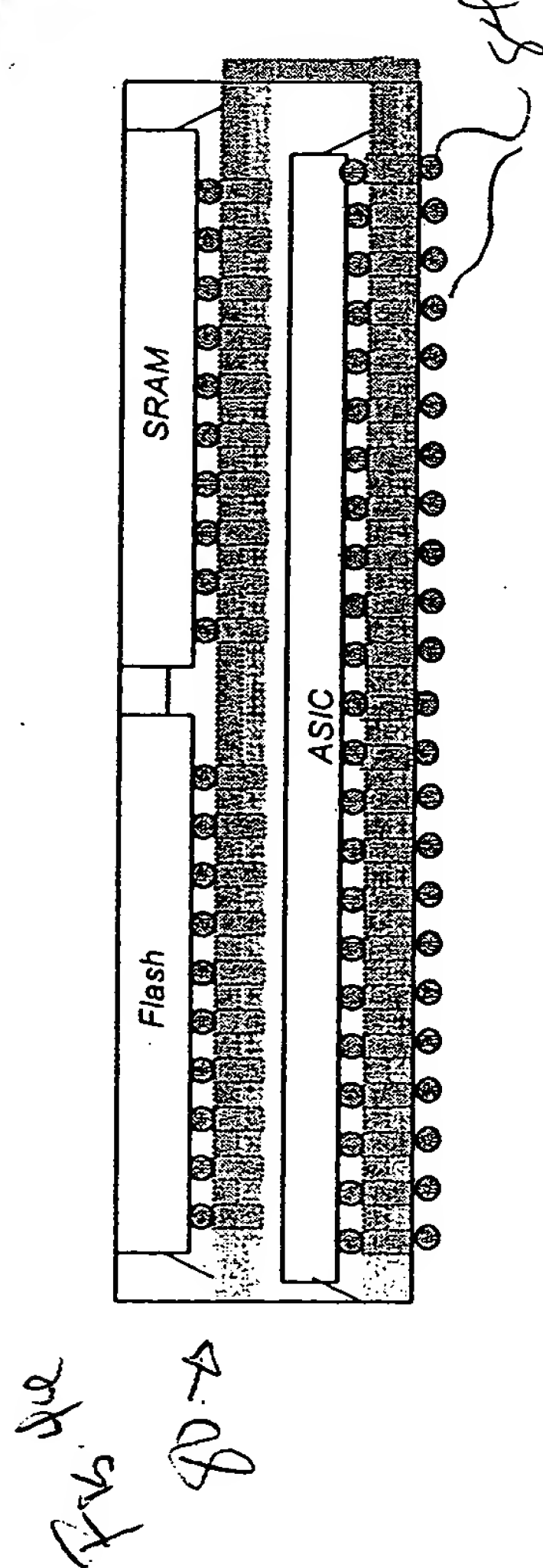
## General Process Steps

4) Thinned and Sawed Assembly



10) Thin Stack Assembly

5) Thinned and Sawed Assembly



## General Process Steps

- 11) Solder Bump Stack
- 12) Singulate (Saw) into Individual Stacks